

Layer	Material	Thickness (nm)	Doping level (cm ⁻³)	Dopant	Comment
26	InGaAs	40	>1x10 ¹⁹	Zn	
25	InGaAs	80	~1x10 ¹⁹	Zn	
24	InP	1500	~1x10 ¹⁸	Zn	
23	InGaAsP	6	~5x10 ¹⁷	Zn	
22	InP	40	~1x10 ¹⁷	Zn	
21	CIL (InGaAs)	(2-5)			Minimal thickness
20	(Al ₉ Ga _{.1}) _{.47} In _{.53} As	40			
19	(Al _{.7} Ga _{.3}) _{.47} In _{.53} As	75			
8 x 6	(Al _{.45} Ga _{.65}) _{.51} In _{.49} As	10			Tensile strained barrier ~-0.3%
7 x 6	(Al _{.25} Ga _{.75}) _{.3} In _{.7} As	6			Compressive strained quantum well ~1.1%
6	(Al _{.45} Ga _{.65}) _{.51} In _{.49} As	10			Tensile strained barrier ~-0.3%
5	(Al _{.7} Ga _{.3}) _{.47} In _{.53} As	75			
4	(Al ₉ Ga _{.1}) _{.47} In _{.53} As	40	1x10 ¹⁸	Si	
3	InP	1500	1x10 ¹⁸	Si	Lower cladding
2	InGaAs	1000	~1x10 ¹⁸	Si	Etch release layer
1	InP	100	1x10 ¹⁸	Si	buffer
	InP substrate			N-type	